

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$ $T_C = +25^{\circ}C$
30V	9.5m $\Omega$ @ $V_{GS} = 10V$	43A
	11.5m $\Omega$ @ $V_{GS} = 4.5V$	39A

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

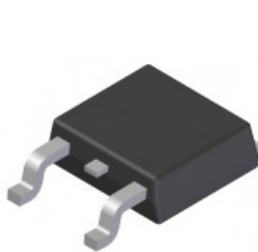
- Backlighting
- DC-DC Converters
- Power Management Functions

## Features

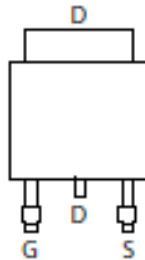
- Low  $R_{DS(ON)}$  – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

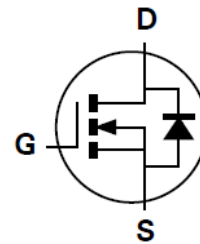
- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.33 grams (approximate)



Top View



Pin Out Top View



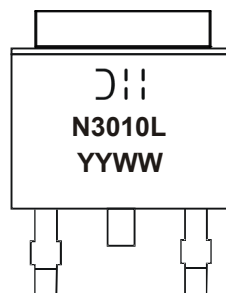
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3010LK3-13	TO252	2500/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



Diodes logo = Manufacturer's Marking  
 N3010L = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Digit of Year (ex: 13 = 2013)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>C</sub> = +25°C T <sub>C</sub> = +70°C	I <sub>D</sub>	43 34	A
	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	13.1 10.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	90	A
Avalanche Current (Notes 7) L = 0.1mH			I <sub>AR</sub>	28	A
Avalanche Energy (Notes 7) L = 0.1mH			E <sub>AR</sub>	40	mJ

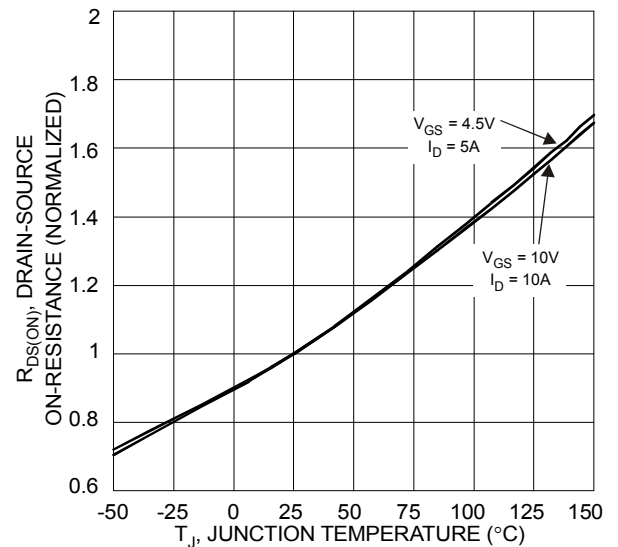
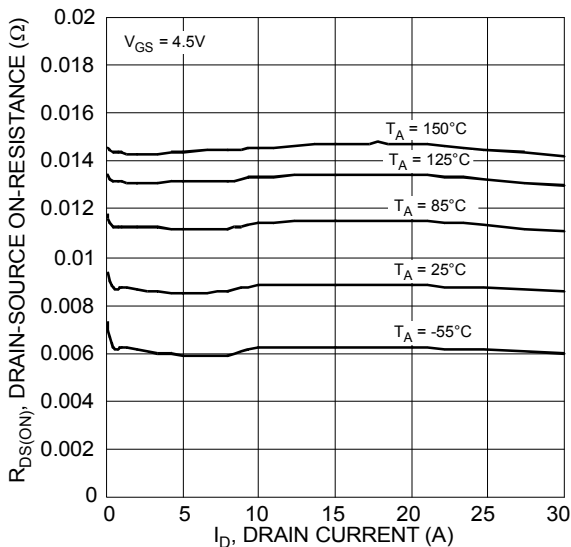
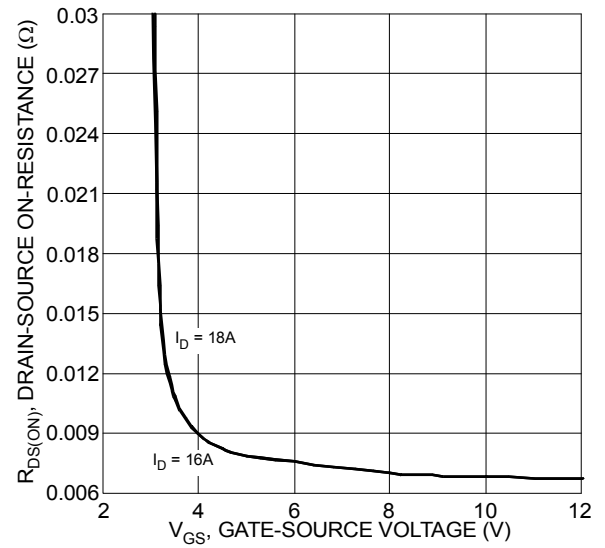
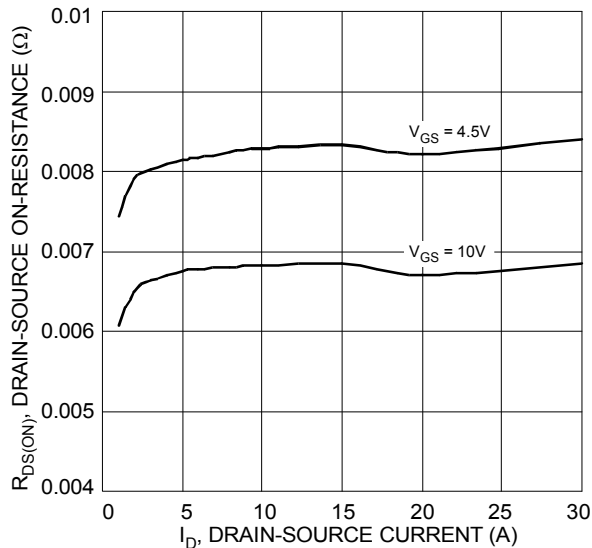
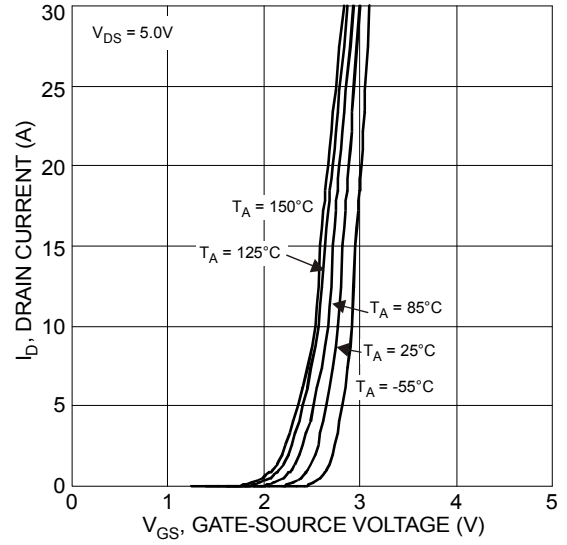
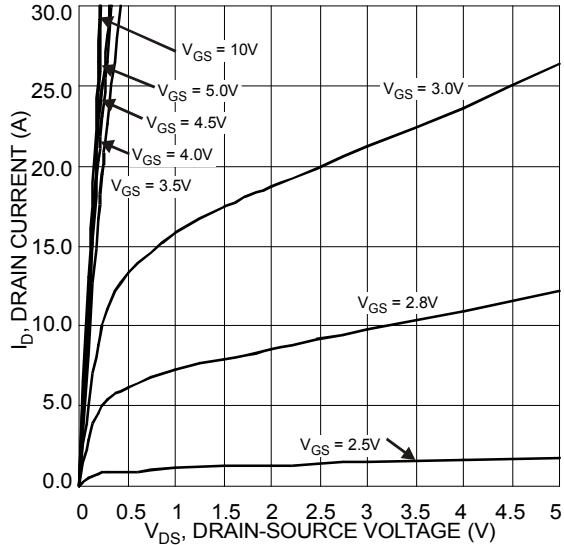
**Thermal Characteristics**

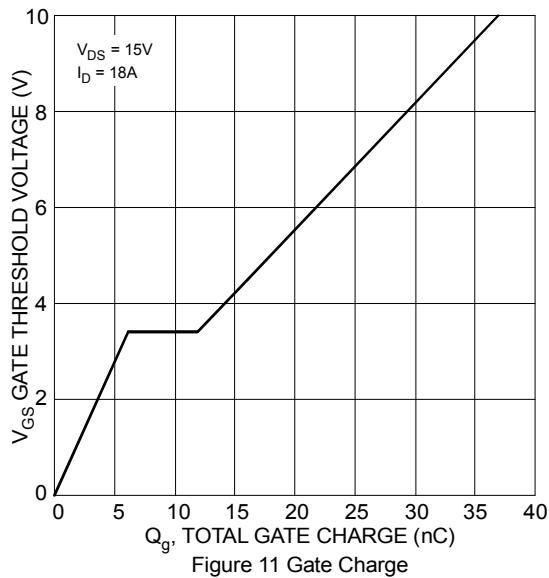
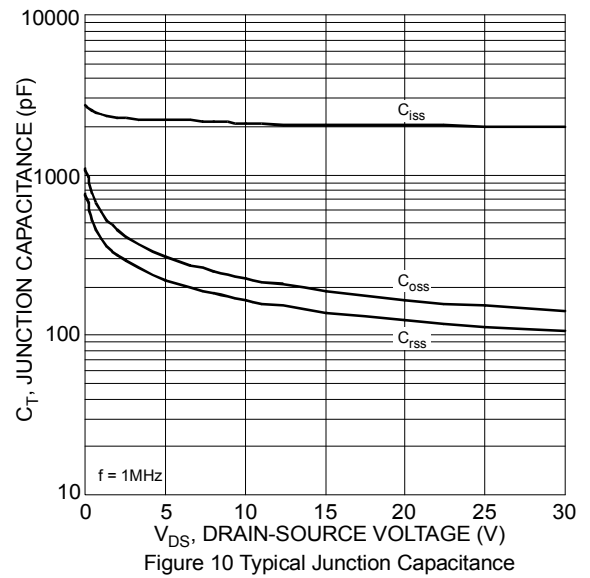
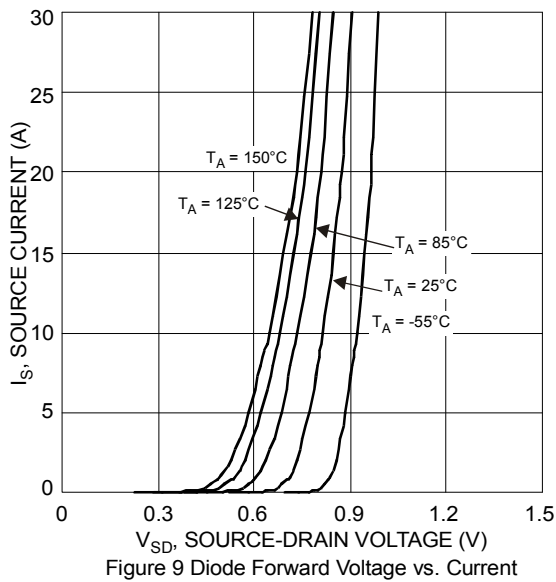
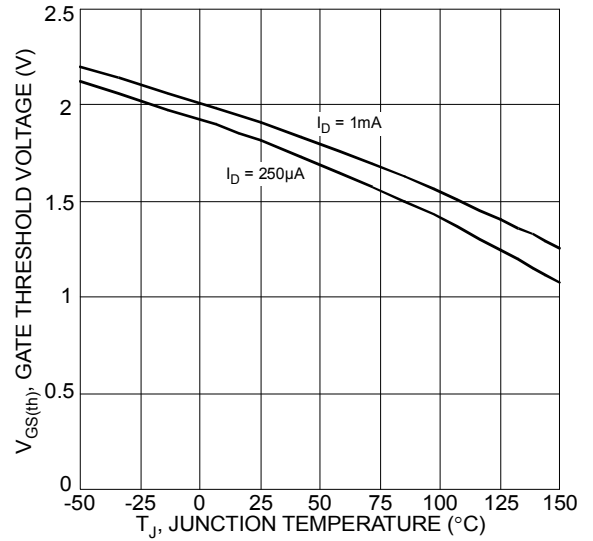
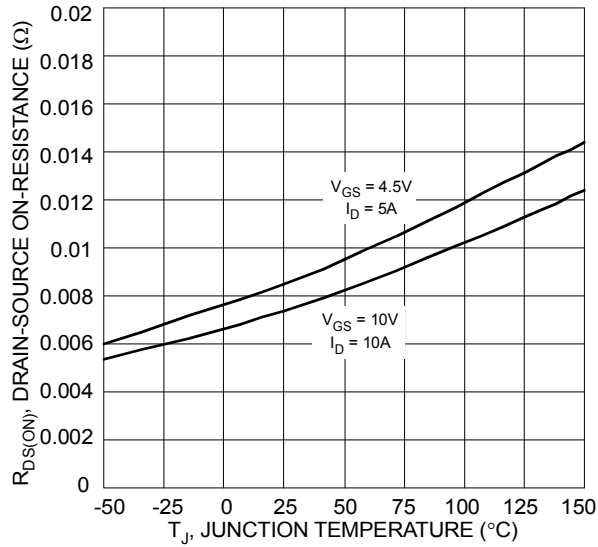
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P <sub>D</sub>	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	78	°C/W
	t < 10s		31	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	51	°C/W
	t < 10s		21	°C/W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	4.7	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

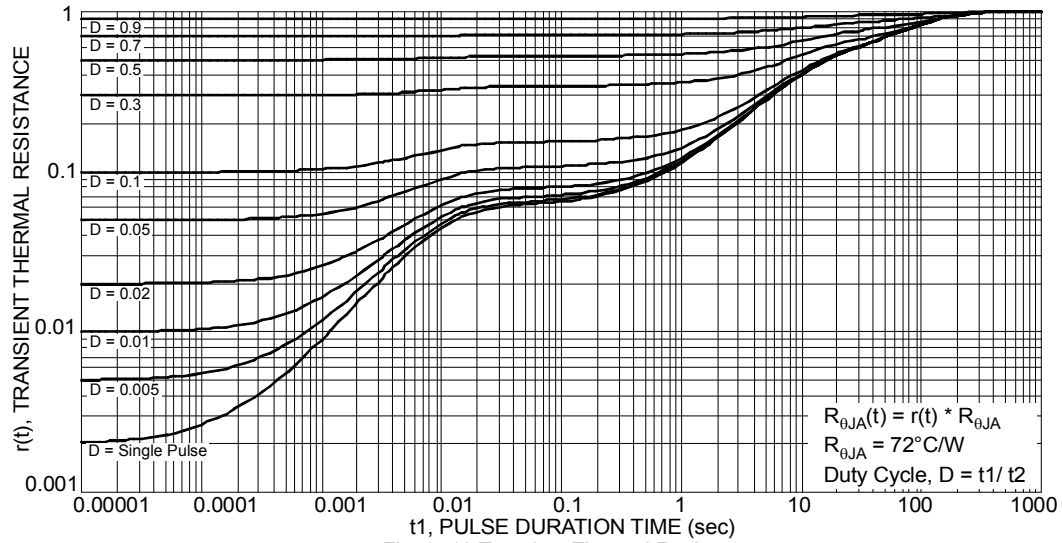
**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	2.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	8	9.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 18A
		—	10	11.5		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 16A
Diode Forward Voltage	V <sub>SD</sub>	—	0.75	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	C <sub>iss</sub>	—	2075	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	190	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	138	—		
Gate resistance	R <sub>g</sub>	—	2.4	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	16.1	—	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 18A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	37	—		
Gate-Source Charge	Q <sub>gs</sub>	—	6.1	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	5.9	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	4.5	—	ns	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, R <sub>L</sub> = 0.83Ω, R <sub>GEN</sub> = 3Ω,
Turn-On Rise Time	t <sub>r</sub>	—	19.6	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	31	—		
Turn-Off Fall Time	t <sub>f</sub>	—	10.7	—		
Reverse Recovery Time	t <sub>rr</sub>	—	13.7	—	ns	I <sub>F</sub> = 15A, di/dt = 500A/µs
Reverse Recovery Charge	Q <sub>rr</sub>	—	18.3	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.  
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.  
7. I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C  
8. Short duration pulse test used to minimize self-heating effect.  
9. Guaranteed by design. Not subject to product testing.

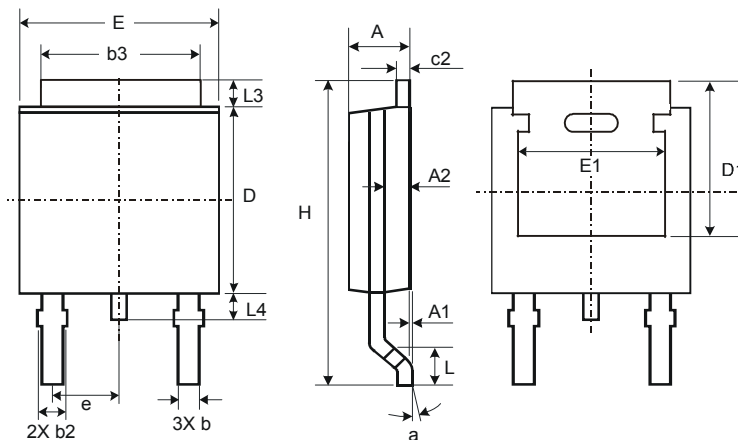






## Package Outline Dimensions

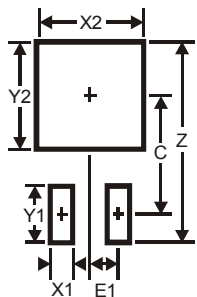
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	—	—
e	—	—	2.286
E	6.45	6.70	6.58
E1	4.32	—	—
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	—
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

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